

Fig 1: Oxford Instruments Plasma Technology FlexAL system configuration, with ICP source, pressure control, substrate biasing.

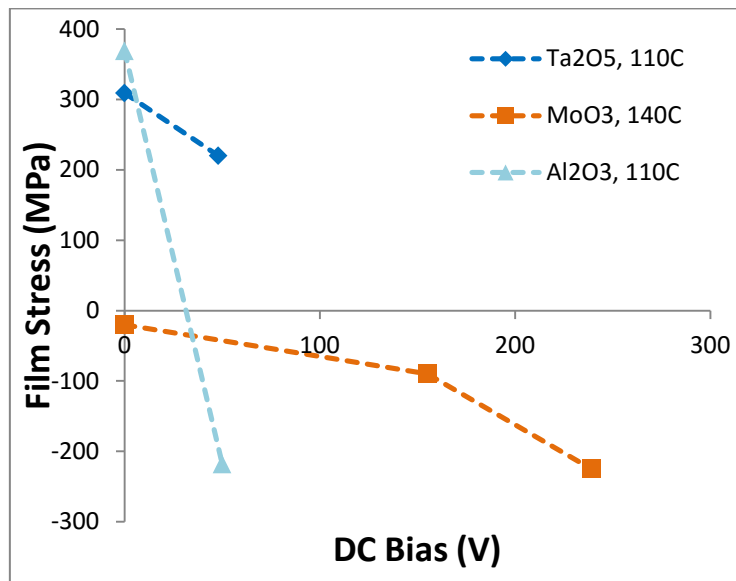


Fig 2: The effects of substrate biasing on film stress for Ta₂O₅, MoO₃ and Al₂O₃ grown by ALD at relatively low temperature.